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Microsemi.

# Power Matters<sup>™</sup>

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## 2N4898 (#23743)

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# Overview Diagrams

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Electrical Rating	Symbol	М	in	Тур	)	Max	Unit
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>					1.30	V
DC Current Gain	HFE	20	0.00			100.00	
Maximum Electrical Rating		Symbol		Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)		V <sub>BR(CB)</sub>	O)			40.00	V
Collector Current (dc)		I <sub>C</sub>				1.00	А
		$V_{CEO}$				40.00	V
Collector-Emitter Voltage (Base Open)							
Collector-Emitter Voltage (Base Open)  Emitter-Base Voltage (Collector Open)		V <sub>EBO</sub>				5.00	V

This part can be found in the following product categories:

- → Discretes → Transistors → BJT( BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices Transistors BJT(BiPolar Junction Transistor) PNPTransistor

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